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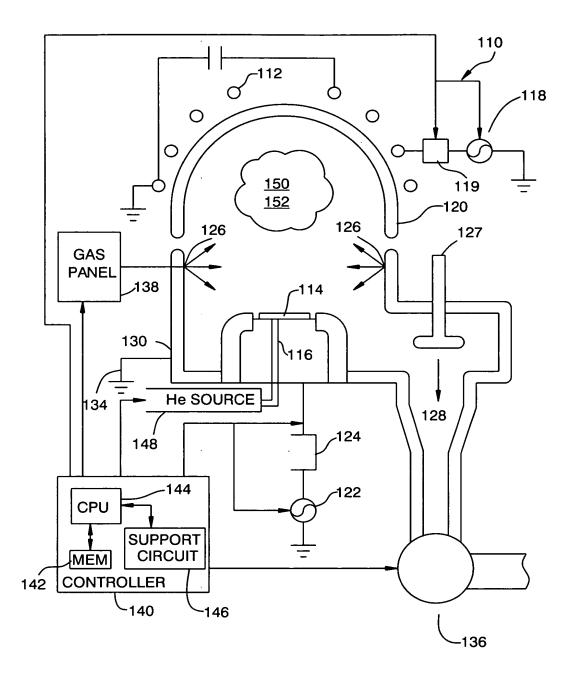


FIG.1
(PRIOR ART)

Sheet 2 of 4
Applicant: Nallan, et al.
Title: METHOD OF PLASMA ETCHING OF HIGHK DIELECTRIC MATERIALS WITH HIGH
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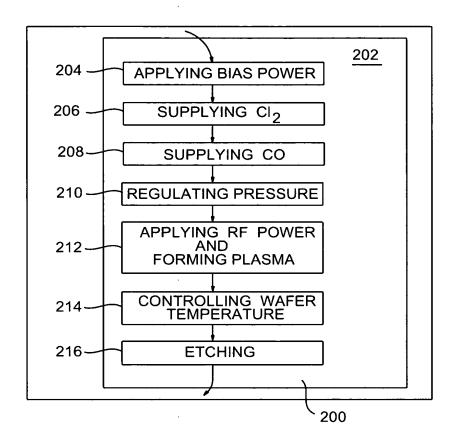
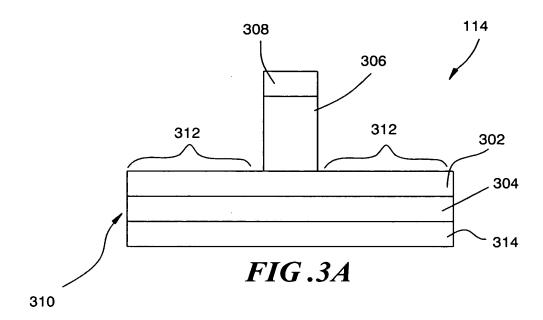


FIG. 2

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Title: METHOD OF PLASMA ETCHING OF HIGHK DIELECTRIC MATERIALS WITH HIGH
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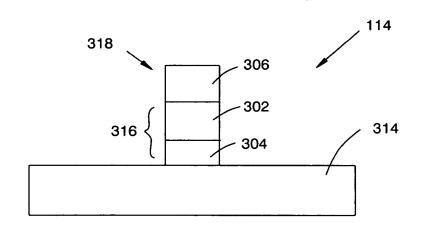


FIG.3B

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Title: METHOD OF PLASMA ETCHING OF HIGHK DIELECTRIC MATERIALS WITH HIGH
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					1
PROCESS OF THE PRESENT INVENTION UTILIZING A DPS CHAMBER					404
PARAMETER	UNITS	RANGE /		PREFERABLY	]
		MIN	MAX		402
Cl <sub>2</sub>	SCCM	20	300	40	
СО	SCCM	2	200	40	
TOTAL PRESSURE	mTORR	2	100	4	
ANTENNA POWER	WATTS	200	2500	1100	
PEDESTAL POWER	WATTS	5	100	20	
PEDESTAL	DEGREES	100	500	350	
TEMPERATURE	CELSIUS	l	<u> </u>	l	J

FIG.4